

# 2600nm InGaAs 1000um PD Chip datasheet

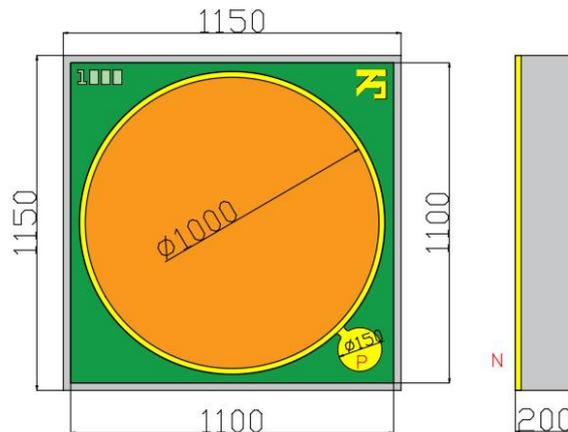
P/N : WIR5-1000

## Application

Optical sensor  
 Gas sensor for CO  
 Optical power meter  
 900-2600nm Spectral range

## Structure

InGaAs / InP PIN Chip.  
 P Electrode (anode) : Gold.  
 N Electrode (cathode) : Gold.



## DIMENSIONS

Conditions	Min.	Typ.	Max	Unit
Active	995	1000	1005	$\mu\text{m}$
Chip width	1130	1150	1170	$\mu\text{m}$
Chip length	1130	1150	1170	$\mu\text{m}$
Chip height	180	200	220	$\mu\text{m}$
Pad Area	140	150	160	$\mu\text{m}$

## Electro-Optical Characteristics ( @ Ta=25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Dark current	$I_d$	$V_r = -0.5V$		900	9000	nA
Responsivity	R	$V_r = 0V, @2300 \text{ nm}$	1.0	1.2	-	A/W
Capacitance	$C_p$	$V_r = 0V, f = 1\text{MHz}$		440	1000	pF
Wavelength range	$\lambda$		900	2330	2600	nm

## ABSOLUTE MAXIMUM RATING

Parameter	Rating
Operating Temperature	-40°C to 85°C
Storage Temperature	-55°C to 125°C
Forward Current	10mA